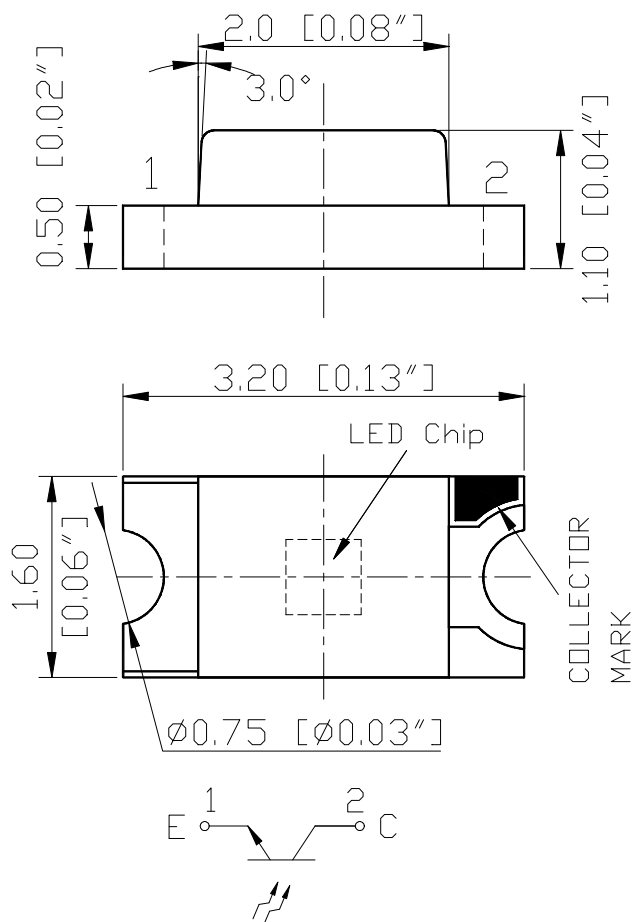


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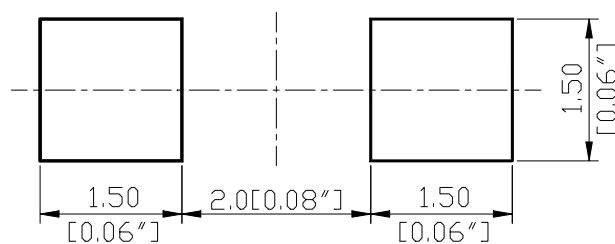
## 光電晶體

Part Number: P150M4

### Package outlines



### RECOMMEND PAD LAYOUT



ITEM	MATERIALS
Resin (mold)	Epoxy
Bonding Wire	Ø 30 µm Au
Lens color	Water transparent
Printed circuit board	BT (white)
Dice	Silicon

#### NOTES:

1. All dimensions are in millimeters (inches);
2. Tolerances are  $\pm 0.1\text{mm}$  (0.004inch) unless otherwise noted.

Rev :	Date	Drawn by :	Checked by :	Approved by :
D	2005-6-7			

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光電晶體

Part Number: P150M4

## Absolute maximum ratings

( $T_A=25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Power dissipation	$P_D$	100	mW
Collector-emitter voltage	$V_{CEO}$	30	V
Emitter-collector voltage	$V_{ECO}$	5	V
Operating temperature range	$T_{OP}$	-20 ~ +80	$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-20 ~ +80	$^\circ\text{C}$

## Electro-optical characteristics

( $T_A=25^\circ\text{C}$ )

Parameter	Test Condition	Symbol	Value			Unit
			Min	Typ	Max	
Collector-emitter breakdown voltage	$I_C = 100\mu\text{A}$ $I_B = 0$	$V_{(BR)CEO}$	30	--	--	V
Emitter-collector breakdown voltage	$I_E = 100\mu\text{A}$ $I_B = 0$	$V_{(BR)ECO}$	5	--	--	V
Collector-emitter saturation voltage	$I_C = 2\text{ mA}$ $I_B = 100\mu\text{A}$	$V_{CE(SAT)}$	--	--	0.3	V
Rise time	$V_{CE} = 5\text{V}$ $I_C = 1\text{ mA}$	$T_R$	--	15	--	$\mu\text{S}$
Fall time	$R_L = 1000\Omega$ $F = 100\text{Hz}$	$T_F$	--	15	--	$\mu\text{S}$
Collector dark current	$V_{CE} = 20\text{V}$ $E_e = 0\text{mW/cm}^2$	$I_{CEO}$	--	--	100	nA
On state collector current	$V_{CE} = 5\text{V}$ , $D=6\text{mm}$ $P_D = 0.5\text{mW}$ $\lambda = 940\text{nm}$ $I_{LED} = 20\text{mA}$	$I_{(ON)}$	1.0	2.0	--	mA

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## 光電晶體

Part Number: P150M4

### OPTICAL CHARACTERISTIC CURVES

FIG.1 COLLECTOR DARK CURRENT VS. AMBIENT TEMPERATURE

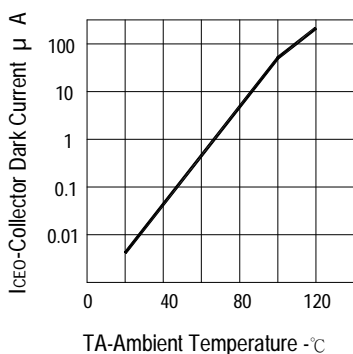


FIG.2 NORMALIZED COLLECTOR CURRENT VS. AMBIENT TEMPERATURE

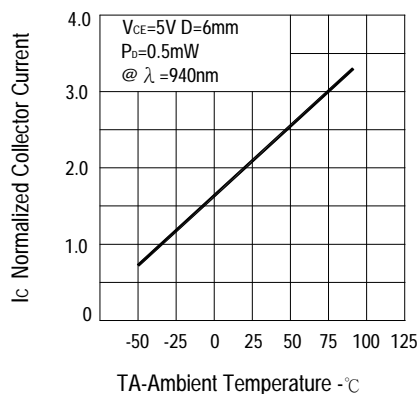


FIG.3 RISE AND FALL TIME VS. LOAD RESISTANCE

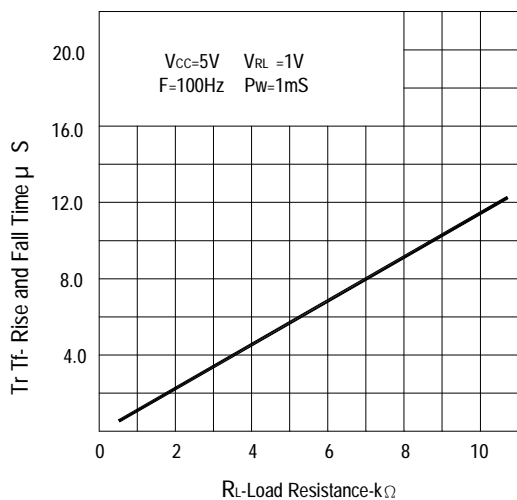
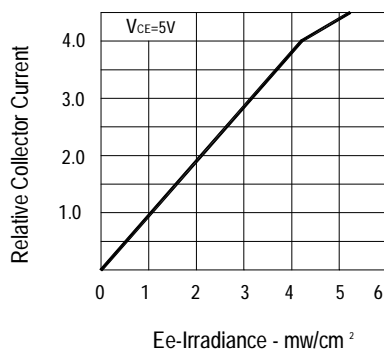
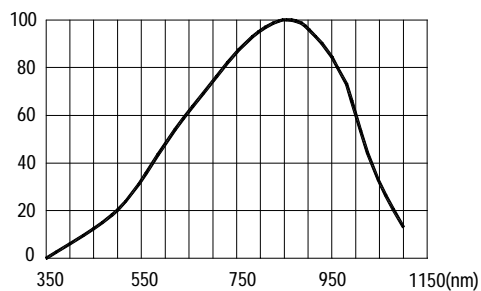


FIG.4 RELATIVE COLLECTOR CURRENT VS. IRRADIANCE



Relative Spectral Response (%)

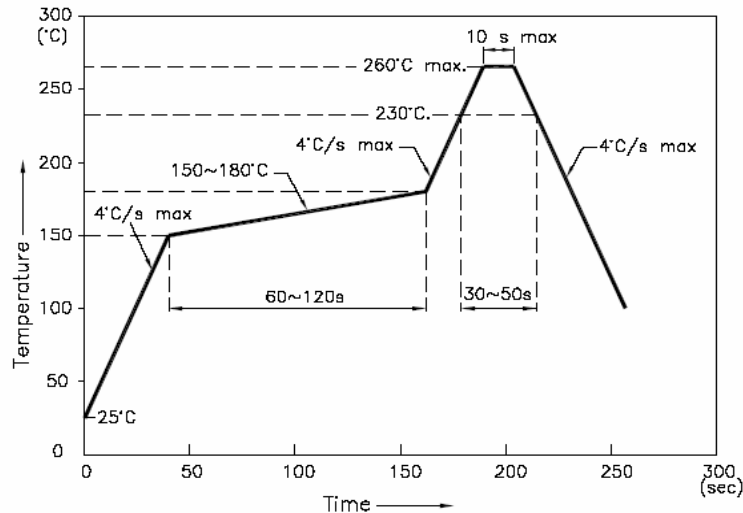


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## 光電晶體

### Reflow Profile

#### ■ Reflow Temp/Time



#### NOTES:

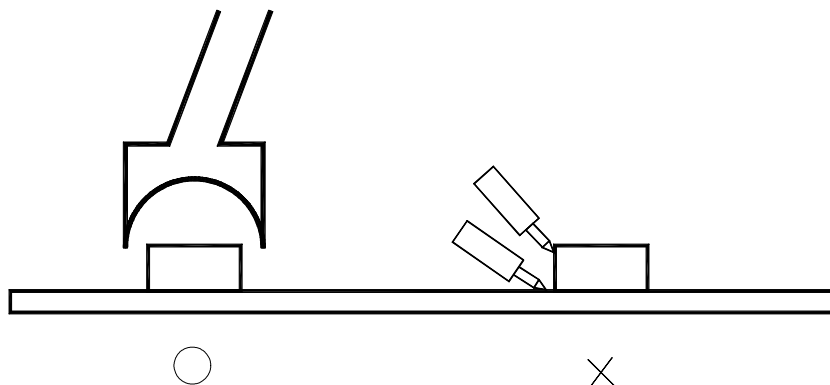
1. We recommend the reflow temperature 245°C (±5°C). the maximum soldering temperature should be limited to 260°C.
2. dont cause stress to the epoxy resin while it is exposed to high temperature.
3. Number of reflow process shall be 2 times or less.

#### ■ Soldering iron

Basic spec is  $\leq 5$ sec when 260°C. If temperature is higher, time should be shorter (+10°C → -1sec). Power dissipation of iron should be smaller than 15W, and temperatures should be controllable. Surface temperature of the device should be under 230°C.

#### ■ Rework

1. Customer must finish rework within 5 sec under 260°C.
2. The head of iron can not touch copper foil
3. Twin-head type is preferred.



# PHOTO TRANSISTOR

## 光電晶體

### Test circuit and handling precautions

#### ■ Handling precautions

##### 1. Over-current-proof

Customer must apply resistors for protection; otherwise slight voltage shift will cause big current change (Burn out will happen).

##### 2.Storage

2.1 It is recommended to store the products in the following conditions:

Humidity: 60% R.H. Max.

Temperature : 5°C ~30°C (41°F ~86°F)

2.2 Shelf life in sealed bag: 12 month at < 5°C ~30°C and < 30% R.H. after the package is Opened, the products should be used within a week or they should be keeping to stored at  $\leq 20$  R.H. with zip-lock sealed.

##### 3.Baking

It is recommended to baking before soldering when the pack is unsealed after 72hrs. The Conditions are as followings:

3.1 60±3°C x(12~24hrs) and < 5%RH, taped reel type

3.2 100±3°C x(45min~1hr), bulk type

3.3 130±3°C x(15~30min), bulk type